

FGA30N120FTD

1200 V, 30 A Field Stop Trench IGBT

Features

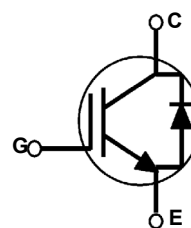
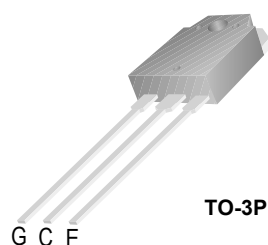
- Field Stop Trench Technology
- High Speed Switching
- Low Saturation Voltage: $V_{CE(sat)} = 1.6 \text{ V @ } I_C = 30 \text{ A}$
- High Input Impedance

General Description

Using advanced field stop trench technology, Fairchild®'s 1200V trench IGBTs offer superior conduction and switching performances for soft switching applications. The device can operate in parallel configuration with exceptional avalanche ruggedness. This device is designed for induction heating and microwave oven.

Applications

- Solar Inverter, UPS, Welder, PFC



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	1200	V
V_{GES}	Gate to Emitter Voltage	± 25	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	60	A
	Collector Current @ $T_C = 100^\circ\text{C}$	30	A
$I_{CM(1)}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	90	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	30	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	339	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	132	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	-	0.38	$^\circ\text{C/W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	-	1.2	$^\circ\text{C/W}$

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^{\circ}\text{C/W}$
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Package Marking and Ordering Information



Device Marking	Device	Package	Eco Status	Packaging Type	Qty per Tube
FGA30N120FTD	FGA30N120FTDTU	TO-3PN	RoHS	Tube	30ea

For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Electrical Characteristics of the IGBT

$T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	1200	-	-	V
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	1	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	±250	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 30mA, V _{CE} = V _{GE}	3.5	6	7.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 30A, V _{GE} = 15V	-	1.6	2	V
		I _C = 30A, V _{GE} = 15V, T _C = 125°C	-	2.0	-	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	-	5140	-	pF
C _{oes}	Output Capacitance		-	150	-	pF
C _{res}	Reverse Transfer Capacitance		-	95	-	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600V, I _C = 30A, R _G = 10Ω, V _{GE} = 15V, Resistive Load, T _C = 25°C	-	31	-	ns
t _r	Rise Time		-	101	-	ns
t _{d(off)}	Turn-Off Delay Time		-	198	-	ns
t _f	Fall Time		-	259	-	ns
E _{on}	Turn-On Switching Loss		-	0.54	-	mJ
E _{off}	Turn-Off Switching Loss		-	1.16	1.51	mJ
E _{ts}	Total Switching Loss	-	1.70	-	mJ	
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600V, I _C = 30A, R _G = 10Ω, V _{GE} = 15V, Resistive Load, T _C = 125°C	-	40	-	ns
t _r	Rise Time		-	127	-	ns
t _{d(off)}	Turn-Off Delay Time		-	211	-	ns
t _f	Fall Time		-	364	-	ns
E _{on}	Turn-On Switching Loss		-	0.74	-	mJ
E _{off}	Turn-Off Switching Loss		-	1.63	-	mJ
E _{ts}	Total Switching Loss		-	2.37	-	mJ
Q _g	Total Gate Charge		V _{CE} = 600V, I _C = 30A, V _{GE} = 15V	-	208	-
Q _{ge}	Gate to Emitter Charge	-		41	-	nC
Q _{gc}	Gate to Collector Charge	-		97	-	nC

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 30A	T _C = 25°C	-	1.3	1.7	V
			T _C = 125°C	-	1.3	-	
t _{rr}	Diode Reverse Recovery Time	I _F =30A, di/dt = 200A/μs	T _C = 25°C	-	730	-	ns
			T _C = 125°C	-	775	-	
I _{rr}	Diode Peak Reverse Recovery Current		T _C = 25°C	-	43	-	A
			T _C = 125°C	-	47	-	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	-	5.9	-	μC
			T _C = 125°C	-	18.2	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

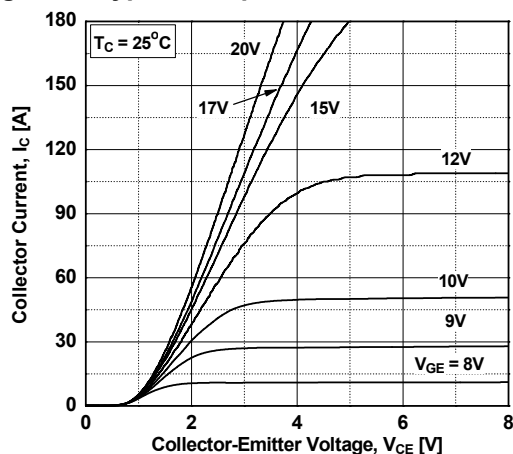


Figure 2. Typical Output Characteristics

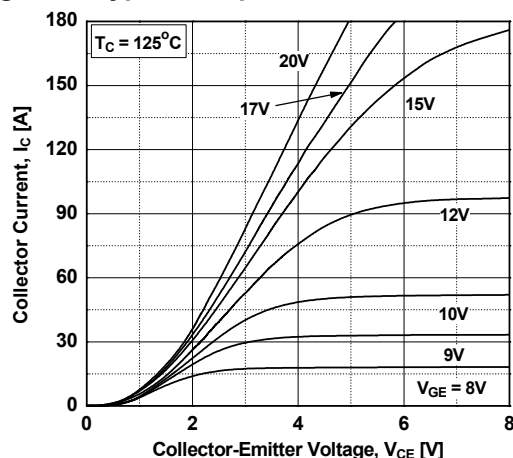


Figure 3. Typical Saturation Voltage Characteristics

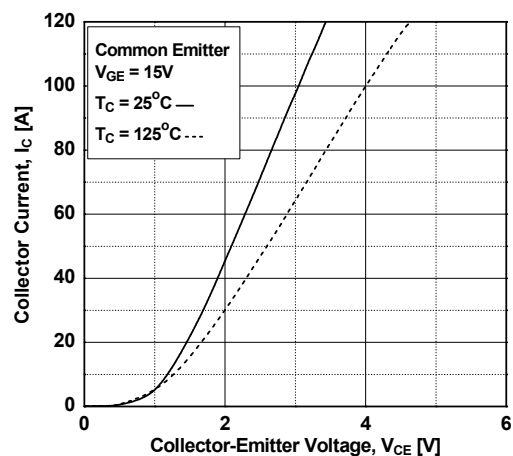


Figure 4. Transfer Characteristics

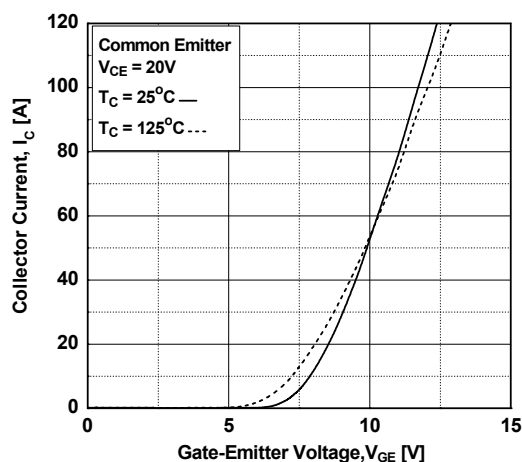


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

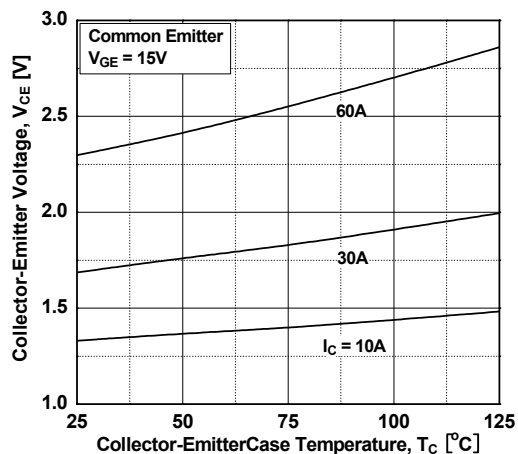
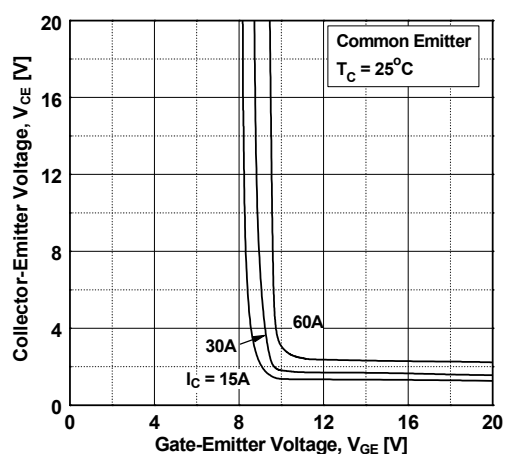


Figure 6. Saturation Voltage vs. V_GE



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

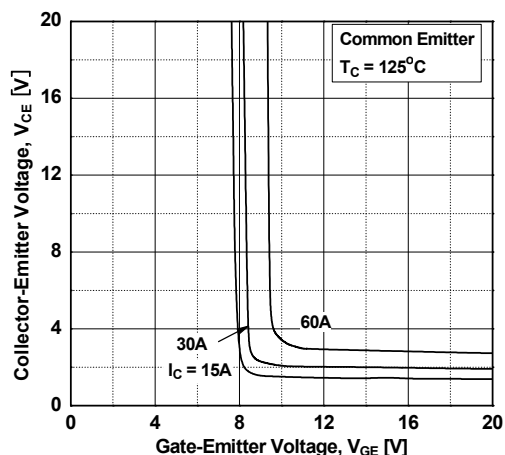


Figure 8. Capacitance Characteristics

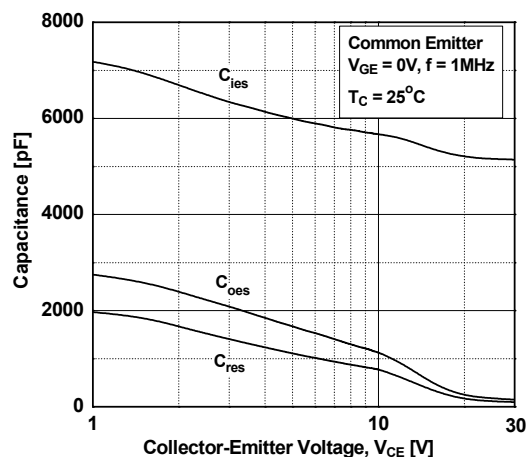


Figure 9. Gate charge Characteristics

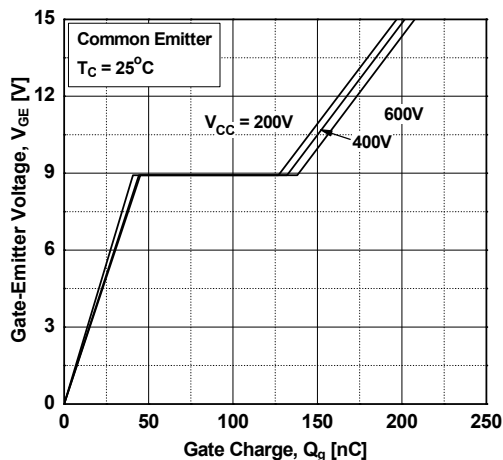


Figure 10. SOA Characteristics

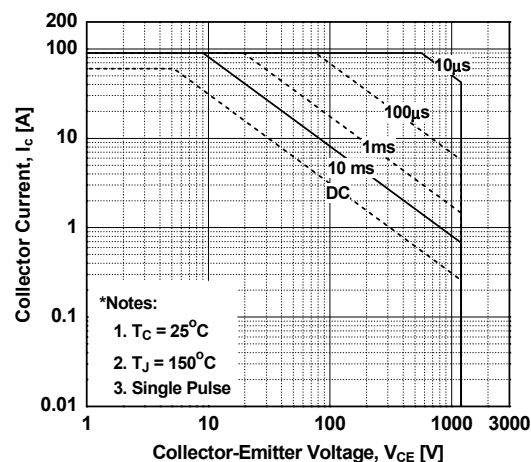


Figure 11. Turn-on Characteristics vs. Gate Resistance

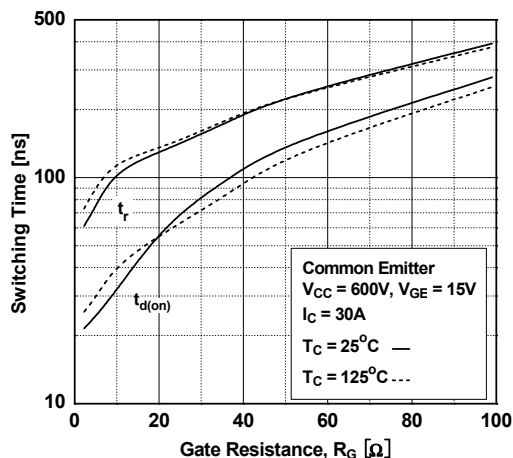
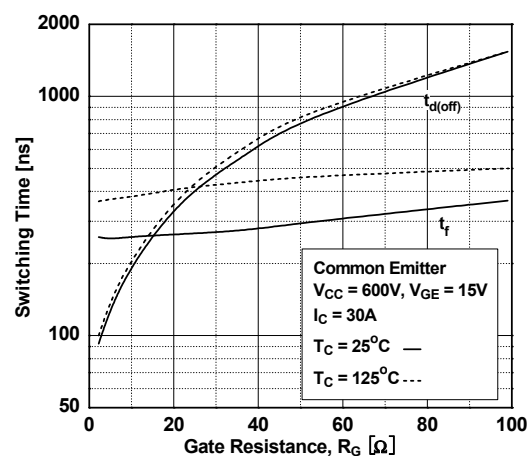


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

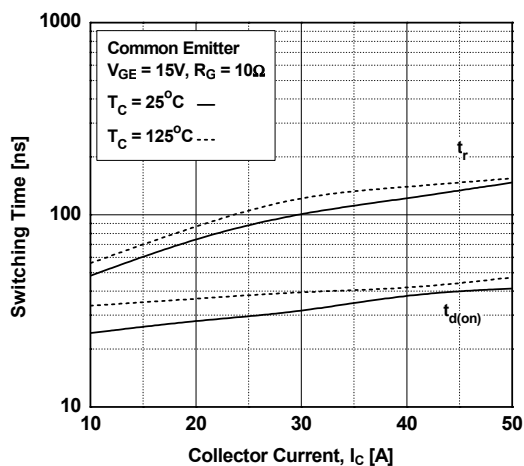


Figure 14. Turn-off Characteristics vs. Collector Current

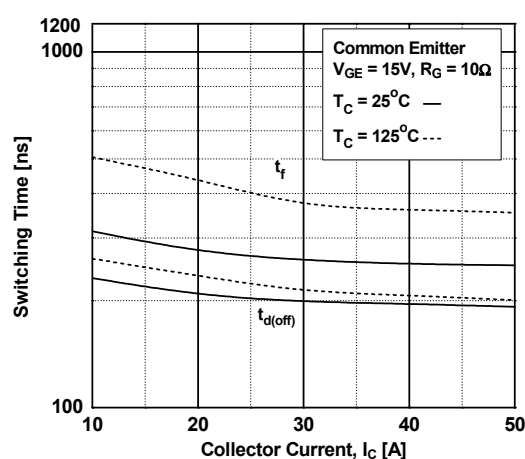


Figure 15. Switching Loss vs. Gate Resistance

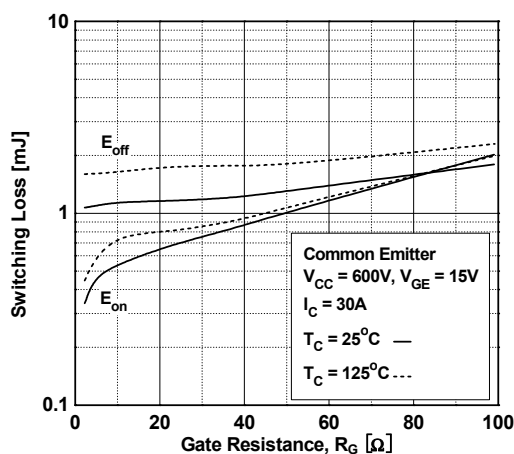


Figure 16. Switching Loss vs. Collector Current

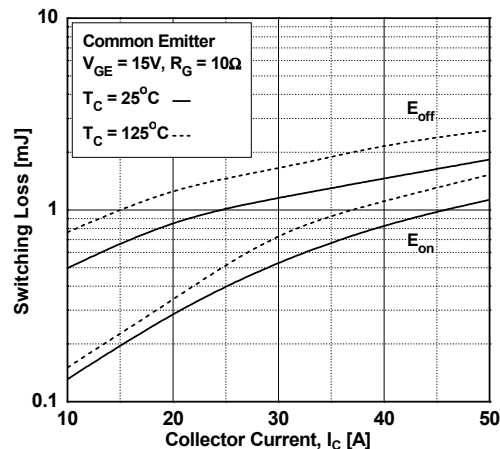


Figure 17. Turn off Switching SOA Characteristics

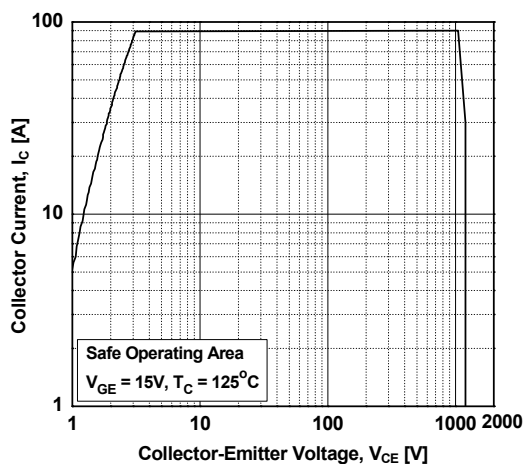
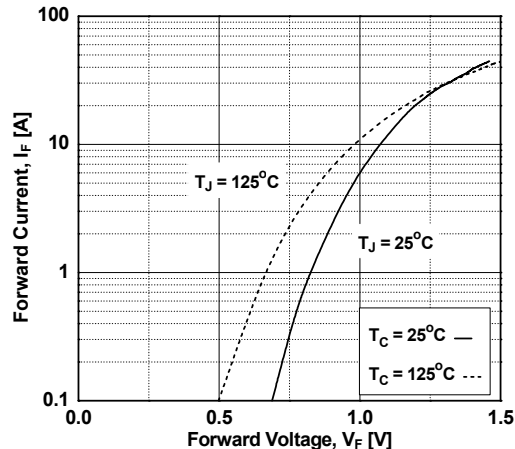


Figure 18. Forward Characteristics



Typical Performance Characteristics

Figure 19. Reverse Current

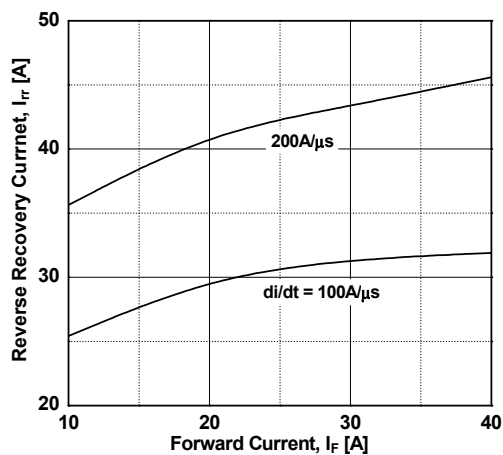


Figure 20. Stored Charge

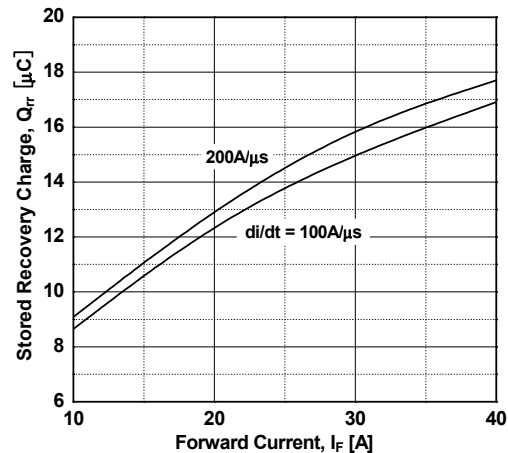


Figure 21. Reverse Recovery Time

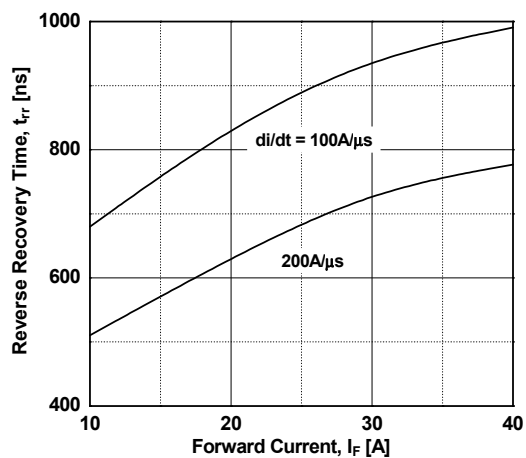
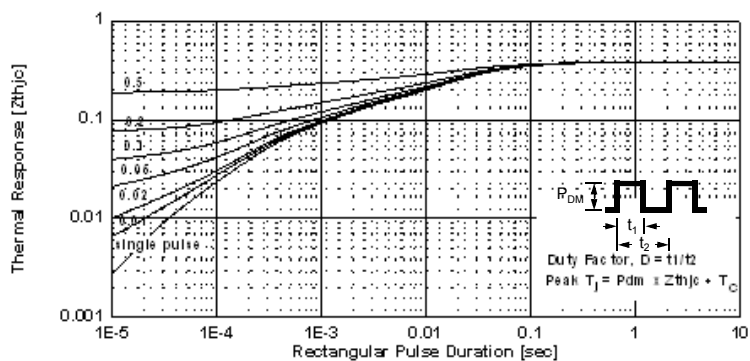
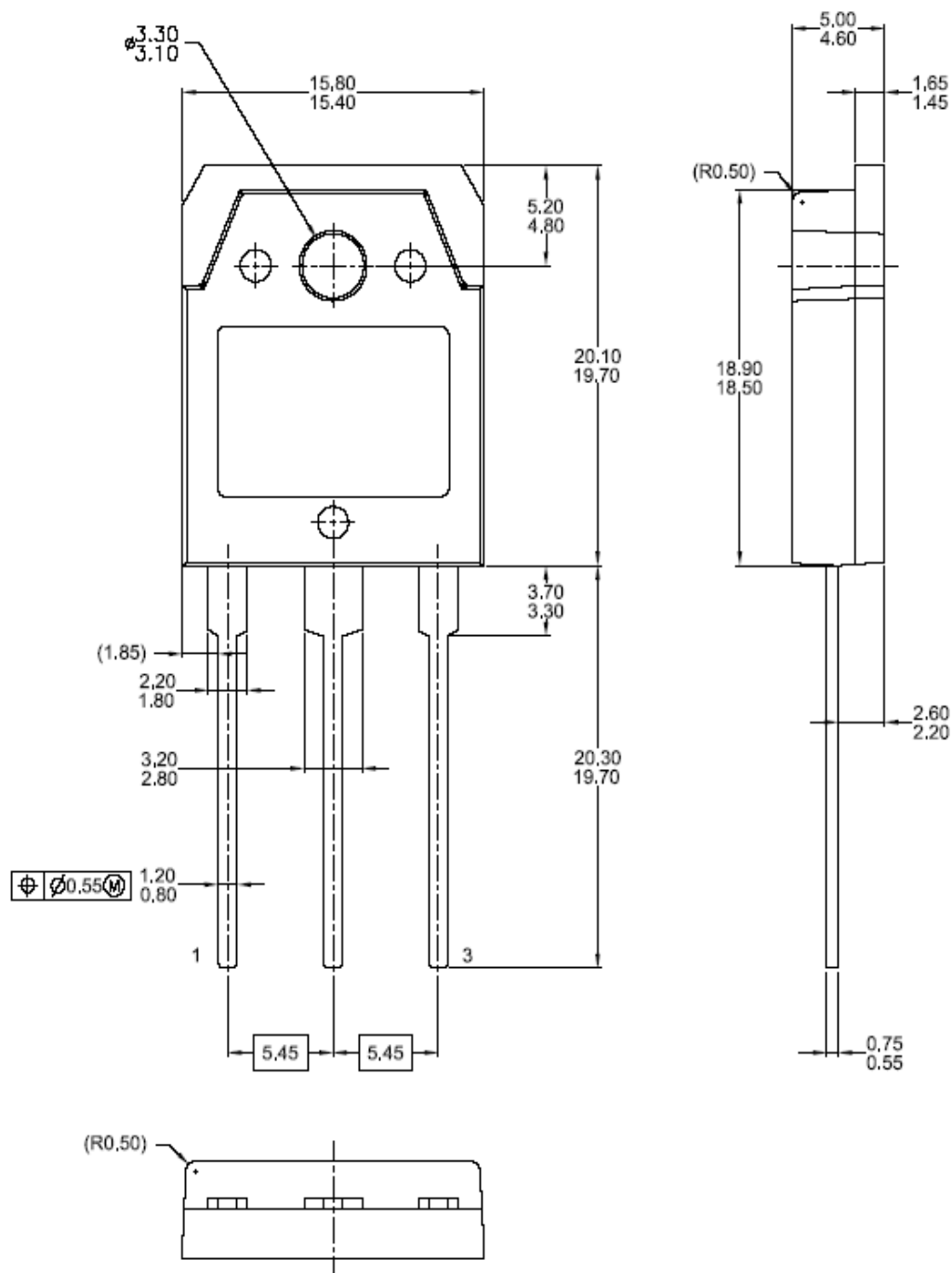


Figure 22. Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-3PN



Dimensions in Millimeters

